



제25회 한국반도체학술대회

The 25th Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 09:00-10:30

Room G (봉래II+III, 6층)

G. Device & Process Modeling, Simulation and Reliability 분과

[WG1-G] Advanced Devices II - Simulation and Reliability

좌장: 김성동 연구위원(SK 하이닉스), 나현철 수석(DB하이텍)

WG1-G-1 09:00-09:15	RF 소자의 고 신뢰성 확보를 위한 RF인가 가속수명 시스템 설계 Yunho Kang, Sungsoo Chung, Sanga Kim, and Namho Kim <i>QRT Incorporated</i>
WG1-G-2 09:15-09:30	New Frequency-Dependent Modeling for Intrinsic Output Admittance of HR PD-SOI MOSFETs Changjo Lee and Seonghearn Lee <i>Department of Electronics Engineering, Hankuk University of Foreign Studies</i>
WG1-G-3 09:30-09:45	Mobility Calculation for GaN based Heterostructure: Effects of Variational Wave Function and Screening Suhyeong Cha and Sung-Min Hong <i>School of Electrical Engineering and Computer Science, GIST</i>
WG1-G-4 09:45-10:00	Characterization of Recombination Lifetime through Above-Bandgap Optical Transfer Curve in InGaAs MOSFETs Junyeap Kim, Heesung Lee, Jaewon Kim, Seong Kwang Kim, Han Bin Yoo, Jaewon Park, Sung-Jin Choi, Dae Hwan Kim, and Dong Myong Kim <i>School of Electrical Engineering, Kookmin University</i>
WG1-G-5 10:00-10:15	Design Optimization of InGaAs/GaAsSb-Based P-type Gate-All-Around Arch-Shaped Tunneling Field-Effect Transistor Bo Gyeong Kim, Jae Hwa Seo, Young Jun Yoon, Min Su Cho, and In Man Kang <i>School of Electronics Engineering, Kyungpook National University</i>
WG1-G-6 10:15-10:30	Analysis of Self Heating Effect Mitigation through STI Material Selection Considering Leakage Current in VFET Ilho Myeong ¹ , Dokyun Son ¹ , Hyunsuk Kim ¹ , Myounggon Kang ² , and Hyungcheol Shin ¹ <i>¹ISRC and the Department of Electrical and Computer Engineering, Seoul National University, ²Department of Electronics Engineering, Korea National University of Transportation</i>